Si Photo Diode Chip--ORT-2128PD

1. Scope：

- The specification applies to NIP silicon photo diode chips.
- Type：ORT-2128PD

2. Structure：

- NIP planar type.
- Top（Cathode）Side：aluminum(Al) alloy.
- Back（Anode）Side：silver(Ag) alloy.

3. Size：(28mil×28mil)

- Chip size ：(670μm × 670μm)± 40μm
- Chip thickness ：280μm ± 25μm
- Active area ：(540μm × 540μm)± 15μm
- Pad size ：(120μm×120μm) ± 10μm
- Pattern drawing：per fig. 1

4. Electro-Optical Characteristics：

(Ta=+25℃)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	I_F=10mA, H=0	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	I_R=100μA, H=0	35			V
Reverse Dark Current	I_D	V_R=10V, H=0			10	nA
Light Current	I_L	V_R=5V,Has1mw/cm^2,@940nm		12		μA
Peak Sensing wavelength	λ_P			940		nm
Junction Capacitance	C_J	V_R=3V, F=1MHz		3		pF

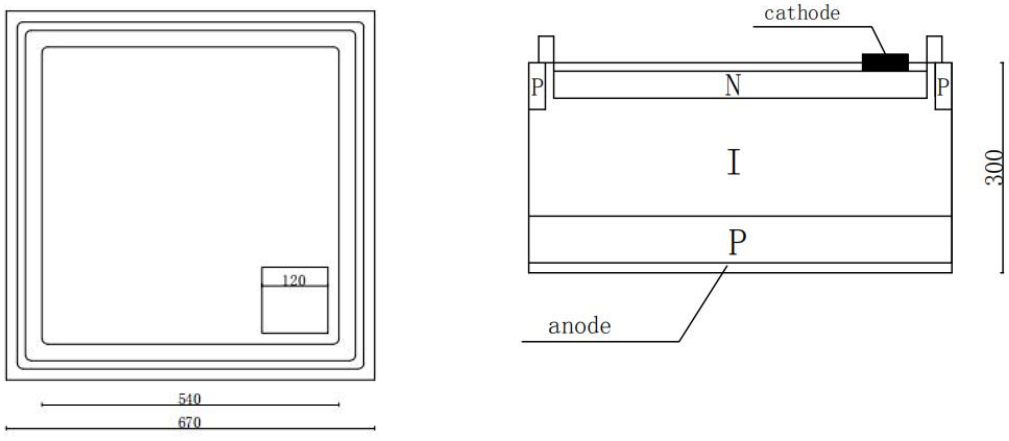

fig.1

5. Spectral Response